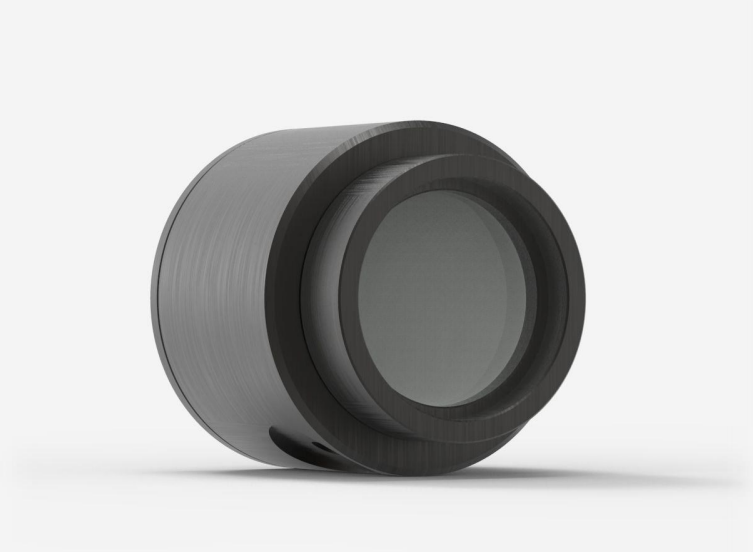
PH100-SI-HA-OD1-D0

Photodiode detector for laser power measurement up to 300 mW.



PRODUCT FAMILY KEY FEATURES

LARGE APERTURES

10 mm Ø for the silicon sensors

3 VERSIONS

- Silicon 350 - 1080 nm, up to 750 mW
- Silicon-UV 210 - 1080 nm, up to 38 mW
- Germanium 800 - 1650 nm, up to 500 mW

CHOICE OF ATTENUATORS

- OD0.3: 50% transmission (for PH100-SI^{UV} only)
- OD1: 10% transmission
- OD2: 1% transmission

HIGH ACCURACY

The new PH100-SI-HA presents the lowest calibration uncertainty to date.

PRECISE CALIBRATION

Wavelength selection in 1 nm steps

SMART INTERFACE

Containing all the calibration data

COMPATIBLE STAND

STAND-D-233

SPECIFICATIONS

MEASUREMENT CAPABILITIES

Maximum average power[1]	300 mW
Noise equivalent power[2]	200 pW
Spectral range	400 - 1080 nm
Typical rise time	0.2 s
Power calibration uncertainty[3]	±5.0 % (400 - 419 nm) ±4.0 % (420 - 899 nm) ±5.0 % (900 - 1009 nm) ±7.5 % (1010 - 1080 nm)
Peak sensitivity	980 nm
Minimum repetition rate[4]	155 kHz

1. At 1064 nm, with attenuator. See curves for maximum power at other wavelengths.
2. At 980 nm. Nominal value. Actual value depends on environmental electromagnetic interference and wavelength.
3. With attenuator. See user manual for calibration uncertainty without attenuator.
4. See user manual for details.

DAMAGE THRESHOLDS

Maximum average power density	100 W/cm²

PHYSICAL CHARACTERISTICS

Aperture diameter	10 mm
Absorber	Si
Dimensions	38.1Ø x 36D mm
Weight	0.14 kg
Distance to sensor face	13.7 mm

ORDERING INFORMATION

PH100-Si-HA-OD1-D0	202683
PH100-Si-HA-OD1-INT-D0	202784
PH100-Si-HA-OD1-IDR-D0	203221

Specifications are subject to change without notice. Refer to the user manual for complete specifications.

INTERESTED IN THIS PRODUCT?

GET A QUOTE

Find your local sales representative at gentec-eo.com/contact-us